Silicon Oxycarbide Accelerated Chemical Vapor Deposition of Graphitic Networks on Ceramic Substrates for Thermal Management Enhancement

Paul D. Garman<sup>1</sup>, Jared M. Johnson<sup>2</sup>, Vishank Talesara<sup>3</sup>, Hao Yang<sup>3</sup>, Dan Zhang<sup>4</sup>, Jose Castro<sup>4</sup>, Wu Lu<sup>3</sup>, Jinwoo Hwang<sup>2</sup> and L. James Lee<sup>1\*</sup>

<sup>1</sup>Department of Chemical and Biomolecular Engineering, <sup>2</sup>Department of Materials

Science and Engineering, <sup>3</sup>Department of Electrical and Computer Engineering,

<sup>4</sup>Department of Integrated Systems Engineering, The Ohio State University, Columbus,

OH 43210

\*Corresponding Author: lee.31@osu.edu

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Figure S1. Optical profilometry of ceramic substrates. Surface profile of Al<sub>2</sub>O<sub>3</sub> (top) and AIN

(bottom) ceramic substrates



Figure S2. Heat transfer set-up for comparison of Al<sub>2</sub>O<sub>3</sub>/AIN coated with graphitic networks



Figure S3. Graphitic networks on quartz. (A) Surface profile of quartz substrate. (B) SEM cross-

section of graphitic networks on quartz



Figure S4. Resistor failure experiment front edge temperature profiles. Front edge temperature profiles of (A) coated  $Al_2O_3$  and (B) bare AIN DBC substrates

Table S1. EELS analysis of sp	p <sup>2</sup> content of graphitic	networks on Al <sub>2</sub> O <sub>3</sub>
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Scan Number	Ι <sub>π</sub> /Ι <sub>π+σ</sub>	sp <sup>2</sup> Content (%)
HOPG	0.1557	100.0
1	0.1471	94.3
2	0.1513	97.0
3	0.1560	100.0
4	0.1560	100.0
5	0.1261	80.8
6	0.1472	94.4

**Movie S1.** SAED analysis of layer orientation boundary in SiOC-accelerated graphitic networks on DBC  $AI_2O_3$ . SAED was carried out over a 100 nm<sup>2</sup> area, with 100 nanodiffraction patterns generated. The patterns are played in succession.